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(54) Title: CHEMICAL MECHANICAL PLANARIZATION SLURRY PROCESSING TECHNIQUES AND SYSTEMS AND METHODS FOR POLISHING SUBSTRATE USING THE SAME

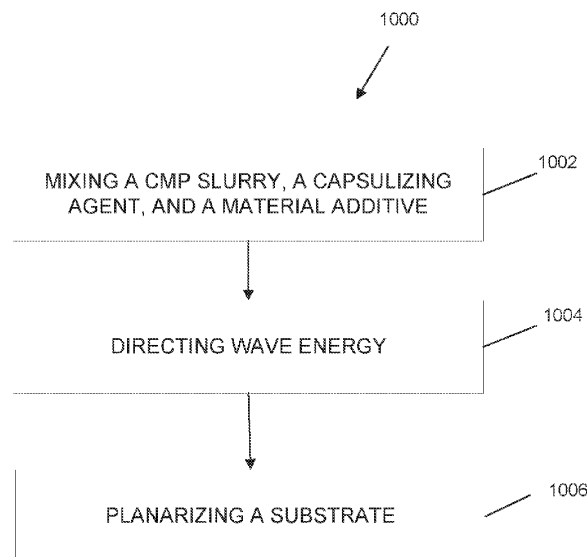


FIG. 10

(57) Abstract: A Chemical Mechanical Planarization (CMP) system, apparatus, and method comprising providing a source of CMP slurry; modifying the source of CMP slurry to form a modified CMP slurry by directing a source of at least one of mechanical or electromagnetic wave energy at the source of CMP slurry; applying a flow of the modified CMP slurry to a wafer polishing apparatus at which a substrate is positioned; and performing a polishing operation on the substrate.

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